

Thyristor

 V_{RRM} 1600 V

32 A

1,21 V

Single Thyristor

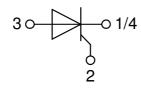
Part number

MCO25-16io1



Backside: isolated

F1 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~ • Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0 Base plate: Copper
- internally DCB isolated
- Advanced power cycling

Terms _Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

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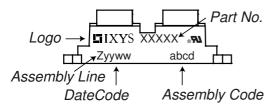
Thyristo		O a sa aliai a sa a		Ì	Ratings		
Symbol	Definition	Conditions	T 0500	min.	typ.	max.	Un
V _{RSM/DSM}	max. non-repetitive reverse/forwa		$T_{VJ} = 25^{\circ}C$			1700	
V _{RRM/DRM}	max. repetitive reverse/forward bl		$T_{VJ} = 25^{\circ}C$			1600	'
I _{R/D}	reverse current, drain current	$V_{R/D} = 1600 \text{ V}$	$T_{VJ} = 25^{\circ}C$			50	μ
		$V_{R/D} = 1600 \text{ V}$	$T_{VJ} = 125^{\circ}C$			2	m
V_{T}	forward voltage drop	$I_T = 25 A$	$T_{VJ} = 25^{\circ}C$			1,23	,
		$I_T = 50 \text{ A}$				1,50	'
		$I_{T} = 25 A$	$T_{VJ} = {}^{\circ}C$			1,21	,
		I _T = 50 A				1,55	1
ITAV	average forward current	$T_C = 80$ °C	$T_{VJ} = 150$ °C			32	1
I _{T(RMS)}	RMS forward current	180° sine				50	,
V _{T0}	threshold voltage		T _{vJ} = 150°C			0,86	,
r _T	slope resistance	oss calculation only				13,9	m۵
R _{thJC}	thermal resistance junction to cas	e				1,1	K/V
R _{thCH}	thermal resistance case to heatsing	nk			0,30		K/V
P _{tot}	total power dissipation		T _C = 25°C			110	٧
I _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			370	,
10111	-	t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			400	,
		t = 10 ms; (50 Hz), sine	T _{v.i} = 150°C			315	,
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			340	,
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			685	A ²
	- Land 10 100 ing	t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			665	A ²
		t = 0.5 ms; (50 Hz), sine	$T_{VJ} = 150^{\circ}C$			495	A ²
		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			480	A ²
C,	junction capacitance	$V_{R} = 400 \text{ V} f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		16	400	pl
			$T_{\rm C} = 150^{\circ}{\rm C}$		10	10	V
P_{GM}	max. gate power dissipation	$t_P = 30 \mu s$	1 _C = 150 C				
_		$t_{P} = 300 \mu s$				1	٧
P _{GAV}	average gate power dissipation					0,5	۷
(di/dt) _{cr}	critical rate of rise of current	$T_{VJ} = 150 ^{\circ}\text{C}; f = 50 \text{Hz}$ re	•			150	A/μ
		$t_P = 200 \mu s; di_G/dt = 0.2 A/\mu s; -$					
			on-repet., $I_T = 30 A$			500	<u> </u>
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150$ °C			1000	V/μ
		R _{GK} = ∞; method 1 (linear volta					
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$			1,5	١
			$T_{VJ} = -40$ °C			1,6	١
I _{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25$ °C			55	m
			$T_{VJ} = -40$ °C			80	m
V _{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$			0,2	١
I _{GD}	gate non-trigger current					5	m
IL	latching current	t _p = 10 μs	$T_{VJ} = 25^{\circ}C$			150	m
-		$I_{G} = 0.2 \text{ A}; \text{ di}_{G}/\text{dt} = 0.2 \text{ A}/\mu\text{s}$					
I _H	holding current	$V_D = 6 \text{ V } R_{GK} = \infty$	T _{vJ} = 25°C			100	m
t _{gd}	gate controlled delay time	$V_{D} = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25$ °C			2	μ
-ga	gant time and anaj amo	$I_{G} = 0.2 \text{ A}; \text{ di}_{G}/\text{dt} = 0.2 \text{ A}/\mu\text{s}$				_	μ
							İ
t _q	turn-off time	\/ _ 100 \/· _ 20 \/· \/ 2	√ T _125°C		150		μ



Package	Package SOT-227B (minibloc)			Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal 1)					150	Α
T _{VJ}	virtual junction temperature	9			-40		150	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		150	°C
Weight						30		g
M _D	mounting torque				1,1		1,5	Nm
\mathbf{M}_{T}	terminal torque				1,1		1,5	Nm
d _{Spp/App}	creepage distance on surface striking distance through air		terminal to terminal	10,5	3,2			mm
d _{Spb/Apb}			terminal to backside	8,6	6,8			mm
V _{ISOL}	isolation voltage	t = 1 second			3000			٧
.002	t = 1 minute		50/60 Hz, RMS; IsoL ≤ 1 mA		2500			٧

¹⁾ I_{hus} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.



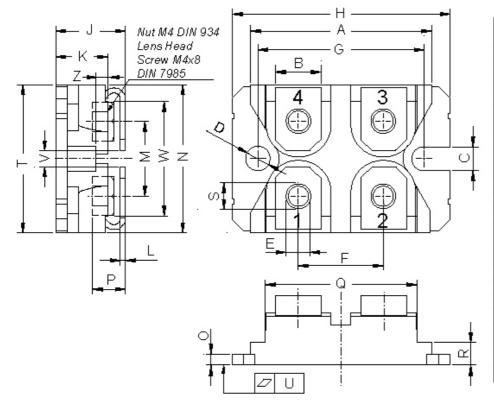


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCO25-16io1	MCO25-16io1	Tube	10	500548

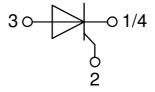
Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150 ^{\circ}\text{C}$
$I \rightarrow V_0$	$-R_0$	Thyristor		
V _{0 max}	threshold voltage	0,86		V
$R_{0 \; \text{max}}$	slope resistance *	12		$m\Omega$



Outlines SOT-227B (minibloc)



Dim	Millimeter		Inches		
Dim.	min	max	min	max	
Α	31.50	31.88	1.240	1.255	
В	7.80	8.20	0.307	0.323	
С	4.09	4.29	0.161	0.169	
D	4.09	4.29	0.161	0.169	
Е	4.09	4.29	0.161	0.169	
F	14.91	15.11	0.587	0.595	
G	30.12	30.30	1.186	1.193	
Н	37.80	38.23	1.488	1.505	
J	11.68	12.22	0.460	0.481	
K	8.92	9.60	0.351	0.378	
L	0.74	0.84	0.029	0.033	
M	12.50	13.10	0.492	0.516	
N	25.15	25.42	0.990	1.001	
0	1.95	2.13	0.077	0.084	
Р	4.95	6.20	0.195	0.244	
Q	26.54	26.90	1.045	1.059	
R	3.94	4.42	0.155	0.167	
S	4.55	4.85	0.179	0.191	
Т	24.59	25.25	0.968	0.994	
U	-0.05	0.10	-0.002	0.004	
V	3.20	5.50	0.126	0.217	
W	19.81	21.08	0.780	0.830	
Ζ	2.50	2.70	0.098	0.106	





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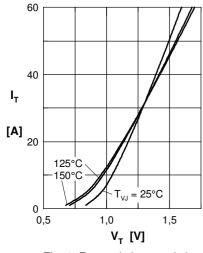


Fig. 1 Forward characteristics

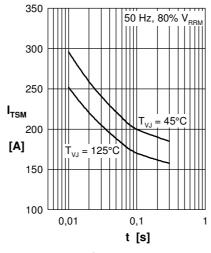


Fig. 2 Surge overload current

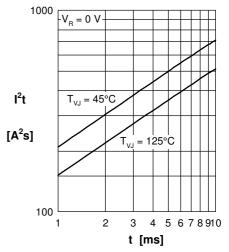


Fig. 3 I²t versus time (1-10 ms)

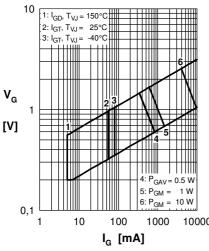


Fig. 4 Gate trigger characteristics

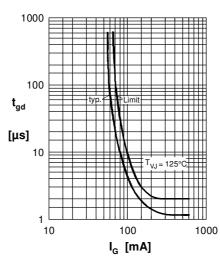


Fig. 5 Gate controlled delay time

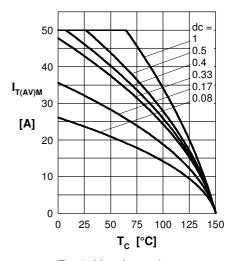


Fig. 6 Max. forward current at case temperature

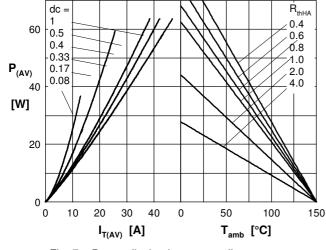


Fig. 7a Power dissipation versus direct output current Fig. 7b and ambient temperature

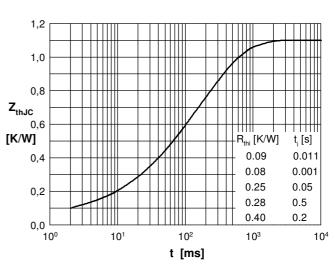


Fig. 8 Transient thermal impedance junction to case

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